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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	833MHz
Co-Processors/DSP	-
RAM Controllers	DDR, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	-
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8541vtapf

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



- 1000 Mbps IEEE 802.3z TBI
- 10/100/1000 Mbps RGMII/RTBI
- Full- and half-duplex support
- Buffer descriptors are backwards compatible with MPC8260 and MPC860T 10/100 programming models
- 9.6-Kbyte jumbo frame support
- RMON statistics support
- 2-Kbyte internal transmit and receive FIFOs
- MII management interface for control and status
- Programmable CRC generation and checking
- OCeaN switch fabric
 - Three-port crossbar packet switch
 - Reorders packets from a source based on priorities
 - Reorders packets to bypass blocked packets
 - Implements starvation avoidance algorithms
 - Supports packets with payloads of up to 256 bytes
- Integrated DMA controller
 - Four-channel controller
 - All channels accessible by both local and remote masters
 - Extended DMA functions (advanced chaining and striding capability)
 - Support for scatter and gather transfers
 - Misaligned transfer capability
 - Interrupt on completed segment, link, list, and error
 - Supports transfers to or from any local memory or I/O port
 - Selectable hardware-enforced coherency (snoop/no-snoop)
 - Ability to start and flow control each DMA channel from external 3-pin interface
 - Ability to launch DMA from single write transaction
- PCI Controllers
 - PCI 2.2 compatible
 - One 64-bit or two 32-bit PCI ports supported at 16 to 66 MHz
 - Host and agent mode support, 64-bit PCI port can be host or agent, if two 32-bit ports, only one can be an agent
 - 64-bit dual address cycle (DAC) support
 - Supports PCI-to-memory and memory-to-PCI streaming
 - Memory prefetching of PCI read accesses
 - Supports posting of processor-to-PCI and PCI-to-memory writes
 - PCI 3.3-V compatible



Electrical Characteristics

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table	1 4	heolu	te Ma	vimum	Ratings	1
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Cha	racteristic	Symbol	Max Value	Unit	Notes
Core supply voltage		V _{DD}	-0.3 to 1.32 0.3 to 1.43 (for 1 GHz only)	V	
PLL supply voltage		AV _{DD}	-0.3 to 1.32 0.3 to 1.43 (for 1 GHz only)	V	
DDR DRAM I/O voltage		GV _{DD}	-0.3 to 3.63	V	
Three-speed Ethernet I/O, N	/II management voltage	LV _{DD}	-0.3 to 3.63 -0.3 to 2.75	V	
CPM, PCI, local bus, DUART, system control and power management, I ² C, and JTAG I/O voltage		OV _{DD}	-0.3 to 3.63	V	3
Input voltage	DDR DRAM signals	MV _{IN}	–0.3 to (GV _{DD} + 0.3)	V	2, 5
	DDR DRAM reference	MV _{REF}	–0.3 to (GV _{DD} + 0.3)	V	2, 5
	Three-speed Ethernet signals	LV _{IN}	–0.3 to (LV _{DD} + 0.3)	V	4, 5
	CPM, Local bus, DUART, SYSCLK, system control and power management, I ² C, and JTAG signals	OV _{IN}	-0.3 to (OV _{DD} + 0.3)1	V	5
	PCI	OV _{IN}	-0.3 to (OV _{DD} + 0.3)	V	6
Storage temperature range		T _{STG}	-55 to 150	°C	

Notes:

- 1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
- 2. Caution: MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- 3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- 4. **Caution:** LV_{IN} must not exceed LV_{DD} by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- 5. (M,L,O)V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.
- 6. OV_{IN} on the PCI interface may overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 3.

2.1.2 Power Sequencing

The MPC8541Erequires its power rails to be applied in a specific sequence in order to ensure proper device operation. These requirements are as follows for power up:

- 1. V_{DD} , AV_{DDn}
- 2. GV_{DD}, LV_{DD}, OV_{DD} (I/O supplies)



6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface.

6.2.1 DDR SDRAM Input AC Timing Specifications

Table 13 provides the input AC timing specifications for the DDR SDRAM interface.

Table 13. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 2.5 V \pm 5%.

Parameter	Symbol	Min	Мах	Unit	Notes
AC input low voltage	V _{IL}	—	MV _{REF} – 0.31	V	_
AC input high voltage	V _{IH}	MV _{REF} + 0.31	GV _{DD} + 0.3	V	_
MDQS—MDQ/MECC input skew per byte	t _{DISKEW}	_		ps	1
For DDR = 333 MHz For DDR \leq 266 MHz			750 1125		

Note:

1. Maximum possible skew between a data strobe (MDQS[n]) and any corresponding bit of data (MDQ[8n + {0...7}] if 0 <= n <= 7) or ECC (MECC[{0...7}] if n = 8).

6.2.2 DDR SDRAM Output AC Timing Specifications

Table 14 and Table 15 provide the output AC timing specifications and measurement conditions for the DDR SDRAM interface.

Table 14. DDR SDRAM Output AC Timing Specifications for Source Synchronous Mode

At recommended operating conditions with GV_{DD} of 2.5 V \pm 5%.

Parameter	Symbol ¹	Min	Мах	Unit	Notes
MCK[n] cycle time, (MCK[n]/MCK[n] crossing)	t _{MCK}	6	10	ns	2
Skew between any MCK to ADDR/CMD 333 MHz 266 MHz 200 MHz	t _{AOSKEW}	-1000 -1100 -1200	200 300 400	ps	3
ADDR/CMD output setup with respect to MCK 333 MHz 266 MHz 200 MHz	t _{DDKHAS}	2.8 3.45 4.6	_	ns	4
ADDR/CMD output hold with respect to MCK 333 MHz 266 MHz 200 MHz	^t DDKHAX	2.0 2.65 3.8	_	ns	4
MCS(n) output setup with respect to MCK 333 MHz 266 MHz 200 MHz	t _{DDKHCS}	2.8 3.45 4.6	_	ns	4



Ethernet: Three-Speed, MII Management

8.2.2.1 GMII Receive AC Timing Specifications

Table 21 provides the GMII receive AC timing specifications.

Table 21. GMII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD} of 3.3 V \pm 5%.

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
RX_CLK clock period	t _{GRX}	—	8.0	—	ns
RX_CLK duty cycle	t _{GRXH} /t _{GRX}	40	—	60	%
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t _{GRDVKH}	2.0	—	—	ns
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t _{GRDXKH}	0.5	—	—	ns
RX_CLK clock rise and fall time	t _{GRXR} , t _{GRXF} ^{2,3}	_		1.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of t(first two letters of functional block)(signal)(state)

(reference)(state) for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

2. Signal timings are measured at 0.7 V and 1.9 V voltage levels.

3. Guaranteed by design.

Figure 8 provides the AC test load for TSEC.



Figure 8. TSEC AC Test Load

Figure 9 shows the GMII receive AC timing diagram.



Figure 9. GMII Receive AC Timing Diagram



8.2.4 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.

8.2.4.1 TBI Transmit AC Timing Specifications

Table 24 provides the MII transmit AC timing specifications.

Table 24. TBI Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD} of 3.3 V \pm 5%.

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
GTX_CLK clock period	t _{TTX}	_	8.0	—	ns
GTX_CLK duty cycle	t _{TTXH} /t _{TTX}	40	_	60	%
GMII data TCG[9:0], TX_ER, TX_EN setup time GTX_CLK going high	^t ttkhdv	2.0	_	—	ns
GMII data TCG[9:0], TX_ER, TX_EN hold time from GTX_CLK going high	^t тткнdx	1.0		—	ns
GTX_CLK clock rise and fall time	t _{TTXR} , t _{TTXF} ^{2,3}	_	_	1.0	ns

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{(first two letters of functional block)(signal)(state)}$

(include to botto or initiate include, include to botto or initiate include, it is a signal (it is the initiate include, it is a signal of the initiate initiat

2. Signal timings are measured at 0.7 V and 1.9 V voltage levels.

3. Guaranteed by design.

Figure 12 shows the TBI transmit AC timing diagram.



Figure 12. TBI Transmit AC Timing Diagram



Ethernet: Three-Speed, MII Management





Figure 14. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, TBI and RTBI are specified in Section 8.1, "Three-Speed Ethernet Controller (TSEC) (10/100/1000 Mbps)—GMII/MII/TBI/RGMII/RTBI Electrical Characteristics."

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in Table 27.

Parameter	Symbol	Conditions		Min	Мах	Unit
Supply voltage (3.3 V)	OV _{DD}	—		3.13	3.47	V
Output high voltage	V _{OH}	I _{OH} = -1.0 mA	$LV_{DD} = Min$	2.10	LV _{DD} + 0.3	V
Output low voltage	V _{OL}	I _{OL} = 1.0 mA	LV _{DD} = Min	GND	0.50	V
Input high voltage	V _{IH}	—		1.70	—	V
Input low voltage	V _{IL}	_		—	0.90	V

Table 27. MII Management DC Electrical Characteristics
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Local Bus

Figure 15 shows the MII management AC timing diagram.



Figure 15. MII Management Interface Timing Diagram

9 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8541E.

9.1 Local Bus DC Electrical Characteristics

Table 29 provides the DC electrical characteristics for the local bus interface.

Parameter	Symbol	Test Condition	Min	Max	Unit
High-level input voltage	V _{IH}	$V_{OUT} \ge V_{OH}$ (min) or	2	OV _{DD} + 0.3	V
Low-level input voltage	VIL	V _{OUT} ≤ V _{OL} (max)	-0.3	0.8	V
Input current	I _{IN}	V_{IN} ¹ = 0 V or V_{IN} = V_{DD}	—	±5	μA
High-level output voltage	V _{OH}	$OV_{DD} = min,$ $I_{OH} = -2mA$	OV _{DD} -0.2	_	V
Low-level output voltage	V _{OL}	OV _{DD} = min, I _{OL} = 2mA	—	0.2	V

Table 29. Local Bus DC Electrical Characteristics

Note:

1. Note that the symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.



Table 30. Local Bus General Timing Parameters—DLL Enabled (continued)

Parameter	Configuration ⁷	Symbol ¹	Min	Мах	Unit	Notes
Local bus clock to output high impedance for	$\overline{LWE[0:1]} = 00$	t _{LBKHOZ2}	—	2.8	ns	5, 9
LAD/EDP	$\overline{LWE[0:1]} = 11$ (default)			4.2		

Notes:

 The symbols used for timing specifications herein follow the pattern of t_{(First two letters of functional block)(signal)(state)} (reference)(state) for inputs and t_(First two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.

- 2. All timings are in reference to LSYNC_IN for DLL enabled mode.
- 3. All signals are measured from $OV_{DD}/2$ of the rising edge of LSYNC_IN for DLL enabled to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
- 4. Input timings are measured at the pin.
- 5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- The value of t_{LBOTOT} is defined as the sum of 1/2 or 1 ccb_clk cycle as programmed by LBCR[AHD], and the number of local bus buffer delays used as programmed at power-on reset with configuration pins LWE[0:1].
- Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at OV_{DD}/2.
- 8. Guaranteed by characterization.
- 9. Guaranteed by design.

Table 31 describes the general timing parameters of the local bus interface of the MPC8541E with the DLL bypassed.

Table 31. Local Bus General Timing Parameters-	-DLL Bypassed
--	---------------

Parameter	Configuration ⁷	Symbol ¹	Min	Max	Unit	Notes
Local bus cycle time	_	t _{LBK}	6.0	—	ns	2
Internal launch/capture clock to LCLK delay	—	t _{LBKHKT}	1.8	3.4	ns	8
LCLK[n] skew to LCLK[m] or LSYNC_OUT	—	t _{LBKSKEW}	_	150	ps	7, 9
Input setup to local bus clock (except LUPWAIT)	—	t _{LBIVKH1}	5.2	—	ns	3, 4
LUPWAIT input setup to local bus clock	—	t _{LBIVKH2}	5.1	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	_	t _{LBIXKH1}	-1.3	_	ns	3, 4
LUPWAIT input hold from local bus clock	—	t _{LBIXKH2}	-0.8	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	—	t _{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except	<u>LWE[0:1]</u> = 00	t _{LBKLOV1}	—	0.5	ns	3
LAD/LDP and LALE)	$\overline{\text{LWE}[0:1]} = 11 \text{ (default)}$			2.0		
Local bus clock to data valid for LAD/LDP	<u>LWE[0:1]</u> = 00	t _{LBKLOV2}	—	0.7	ns	3
	$\overline{\text{LWE}[0:1]} = 11 \text{ (default)}$			2.2	Ĩ	







Figure 20. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Bypass Mode)



Local Bus



Figure 21. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 or 8 (DLL Enabled)



СРМ

10 CPM

This section describes the DC and AC electrical specifications for the CPM of the MPC8541E.

10.1 CPM DC Electrical Characteristics

Table 32 provides the DC electrical characteristics for the CPM.

Characteristic	Symbol	Condition	Min	Мах	Unit	Notes
Input high voltage	V _{IH}		2.0	3.465	V	1
Input low voltage	V _{IL}		GND	0.8	V	1, 2
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	—	V	1
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	—	0.5	V	1
Output high voltage	V _{OH}	I _{OH} = -2.0 mA	2.4	—	V	1
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	—	0.4	V	1

Table 32. CPM DC Electrical Characteristics

10.2 CPM AC Timing Specifications

Table 33 and Table 34 provide the CPM input and output AC timing specifications, respectively.

NOTE: Rise/Fall Time on CPM Input Pins

It is recommended that the rise/fall time on CPM input pins should not exceed 5 ns. This should be enforced especially on clock signals. Rise time refers to signal transitions from 10% to 90% of VCC; fall time refers to transitions from 90% to 10% of VCC.

Characteristic	Symbol ²	Min ³	Unit
FCC inputs—internal clock (NMSI) input setup time	t _{FIIVKH}	6	ns
FCC inputs—internal clock (NMSI) hold time	t _{FIIXKH}	0	ns
FCC inputs—external clock (NMSI) input setup time	t _{FEIVKH}	2.5	ns
FCC inputs—external clock (NMSI) hold time	t _{FEIXKH} b	2	ns
SPI inputs—internal clock (NMSI) input setup time	t _{NIIVKH}	6	ns
SPI inputs—internal clock (NMSI) input hold time	t _{NIIXKH}	0	ns
SPI inputs—external clock (NMSI) input setup time	t _{NEIVKH}	4	ns
SPI inputs—external clock (NMSI) input hold time	t _{NEIXKH}	2	ns
PIO inputs—input setup time	t _{PIIVKH}	8	ns

Table 33. CPM Input AC Timing Specifications ¹



Table 33. CPM Input AC Timing Specifications ¹ (continued)

Notes:

- 1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
- 2. The symbols used for timing specifications herein follow the pattern of t_{(first two letters of functional block)(signal)(state)} (reference)(state) for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{FIIVKH} symbolizes the FCC inputs internal timing (FI) with respect to the time the input signals (I) reaching the valid state (V) relative to the reference clock t_{FCC} (K) going to the high (H) state or setup time.
- 3. PIO and TIMER inputs and outputs are asynchronous to SYSCLK or any other externally visible clock. PIO/TIMER inputs are internally synchronized to the CPM internal clock. PIO/TIMER outputs should be treated as asynchronous.

Characteristic	Symbol ²	Min	Max	Unit
FCC outputs—internal clock (NMSI) delay	t _{FIKHOX}	1	5.5	ns
FCC outputs—external clock (NMSI) delay	t _{FEKHOX}	2	8	ns
SPI outputs—internal clock (NMSI) delay	t _{NIKHOX}	0.5	10	ns
SPI outputs—external clock (NMSI) delay	t _{NEKHOX}	2	8	ns
PIO outputs delay	t _{PIKHOX}	1	11	ns

Table 34. CPM Output AC Timing Specifications ¹

Notes:

- 1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
- The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state) (reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{FIKHOX} symbolizes the FCC inputs internal timing (FI) for the time t_{FCC} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).
 </sub>

Figure 23 provides the AC test load for the CPM.



Figure 23. CPM AC Test Load

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СРМ



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Figure 24 through Figure 29 represent the AC timing from Table 33 and Table 34. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

Figure 24 shows the FCC internal clock.



Figure 24. FCC Internal AC Timing Clock Diagram

Figure 25 shows the FCC external clock.



Figure 25. FCC External AC Timing Clock Diagram

Figure 26 shows Ethernet collision timing on FCCs.



Figure 26. Ethernet Collision AC Timing Diagram (FCC)



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10.3 CPM I2C AC Specification

Table 35. I2C Timing

Characteristic	Expression	All Freq	All Frequencies				
Characteristic	Expression	Min	Мах	Unit			
SCL clock frequency (slave)	f _{SCL}	0	F _{MAX} ⁽¹⁾	Hz			
SCL clock frequency (master)	f _{SCL}	BRGCLK/16512	BRGCLK/48	Hz			
Bus free time between transmissions	t _{SDHDL}	1/(2.2 * f _{SCL})	—	S			
Low period of SCL	t _{SCLCH}	1/(2.2 * f _{SCL})	—	S			
High period of SCL	tSCHCL	1/(2.2 * f _{SCL})	—	S			
Start condition setup time ²	tSCHDL	2/(divider * f _{SCL})	(2)	S			
Start condition hold time ²	t _{SDLCL}	3/(divider * f _{SCL})	—	S			
Data hold time ²	t _{SCLDX}	2/(divider * f _{SCL})	—	S			
Data setup time ²	t _{SDVCH}	3/(divider * f _{SCL})	—	S			
SDA/SCL rise time	t _{SRISE}	—	1/(10 * f _{SCL})	S			
SDA/SCL fall time	t _{SFALL}	—	1/(33 * f _{SCL})	S			
Stop condition setup time	t _{SCHDH}	2/(divider * f _{SCL})	—	S			

Notes:

1. F_{MAX} = BRGCLK/(min_divider*prescale. Where prescaler=25-I2MODE[PDIV]; and min_divider=12 if digital filter disabled and 18 if enabled.

Example #1: if I2MODE[PDIV]=11 (prescaler=4) and I2MODE[FLT]=0 (digital filter disabled) then FMAX=BRGCLK/48 Example #2: if I2MODE[PDIV]=00 (prescaler=32) and I2MODE[FLT]=1 (digital filter enabled) then FMAX=BRGCLK/576 2. divider = f_{SCL}/prescaler.

In master mode: divider=BRGCLK/(f_{SCL}*prescaler)=2*(I2BRG[DIV]+3)

In slave mode: divider=BRGCLK/(f_{SCL}*prescaler)



Figure 30. CPM I2C Bus Timing Diagram



Package and Pin Listings

Table 43.	MPC8541E	Pinout Listing	(continued)	١
		I mout Listing	(continucu)	,

Signal	Signal Package Pin Number			Notes
	JTAG			
тск	AF21	Ι	OV _{DD}	—
TDI	AG21	Ι	OV _{DD}	12
TDO	AF19	0	OV _{DD}	11
TMS	AF23	I	OV _{DD}	12
TRST	AG23	I	OV _{DD}	12
	DFT			
LSSD_MODE	AG19	Ι	OV _{DD}	20
L1_TSTCLK	AB22	Ι	OV _{DD}	20
L2_TSTCLK	AG22	Ι	OV _{DD}	20
TEST_SEL0	AH20	Ι	OV _{DD}	3
TEST_SEL1	AG26	I	OV _{DD}	3
	Thermal Management			
THERM0	AG2	_		14
THERM1	AH3	_	_	14
	Power Management			
ASLEEP	AG18		—	9, 18
	Power and Ground Signals			
AV _{DD} 1	AH19	Power for e500 PLL (1.2 V)	AV _{DD} 1	—
AV _{DD} 2	AH18	Power for CCB PLL (1.2 V)	AV _{DD} 2	—
AV _{DD} 3	AH17	Power for CPM PLL (1.2 V)	AV _{DD} 3	_
AV _{DD} 4	AF28	Power for PCI1 PLL (1.2 V)	AV _{DD} 4	-
AV _{DD} 5	AE28	Power for PCI2 PLL (1.2 V)	AV _{DD} 5	—



15 Clocking

This section describes the PLL configuration of the MPC8541E. Note that the platform clock is identical to the CCB clock.

15.1 Clock Ranges

Table 44 provides the clocking specifications for the processor core and Table 44 provides the clocking specifications for the memory bus.

Characteristic	Maximum Processor Core Frequency											
	533 MHz		600	600 MHz 667 MHz		667 MHz		MHz	1000 MHz		Unit	Notes
	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
e500 core processor frequency	400	533	400	600	400	667	400	833	400	1000	MHz	1, 2, 3

Table 44. Processor Core Clocking Specifications

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 15.2, "Platform/System PLL Ratio," and Section 15.3, "e500 Core PLL Ratio," for ratio settings.

2.) The minimum e500 core frequency is based on the minimum platform frequency of 200 MHz.

3. 1000 MHz frequency supports only a 1.3 V core.

Table 45. Memory Bus Clocking Specifications

Characteristic	Maximum Pro Frequ 533, 600, 667,	Unit	Notes	
	Min	Мах		
Memory bus frequency	100	166	MHz	1, 2, 3

Notes:

- 1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 15.2, "Platform/System PLL Ratio," and Section 15.3, "e500 Core PLL Ratio," for ratio settings.
- 2. The memory bus speed is half of the DDR data rate, hence, half of the platform clock frequency.
- 3. 1000 MHz frequency supports only a 1.3 V core.



Clocking

15.3 e500 Core PLL Ratio

Table 47 describes the clock ratio between the e500 core complex bus (CCB) and the e500 core clock. This ratio is determined by the binary value of LALE and LGPL2 at power up, as shown in Table 47.

Binary Value of LALE, LGPL2 Signals	Ratio Description
00	2:1 e500 core:CCB
01	5:2 e500 core:CCB
10	3:1 e500 core:CCB
11	7:2 e500 core:CCB

Table 47. e500 Core to CCB Ratio

15.4 Frequency Options

Table 48 shows the expected frequency values for the platform frequency when using a CCB to SYSCLK ratio in comparison to the memory bus speed.

Table 48. Frequency Options with Respect to Memory Bus Speeds

CCB to SYSCLK Ratio	SYSCLK (MHz)									
	17	25	33	42	67	83	100	111	133	
		Platform/CCB Frequency (MHz)								
2							200	222	267	
3					200	250	300	333		
4					267	333		•	<u>.</u>	
5				208	333		1			
6			200	250		4				
8		200	267	333						
9		225	300		2					
10	1	250	333	1						
12	200	300		-						
16	267									



17.6 Configuration Pin Multiplexing

The MPC8541E provides the user with power-on configuration options which can be set through the use of external pull-up or pull-down resistors of 4.7 k Ω on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.

While $\overline{\text{HRESET}}$ is asserted however, these pins are treated as inputs. The value presented on these pins while $\overline{\text{HRESET}}$ is asserted, is latched when $\overline{\text{HRESET}}$ deasserts, at which time the input receiver is disabled and the I/O circuit takes on its normal function. Most of these sampled configuration pins are equipped with an on-chip gated resistor of approximately $20 \text{ k}\Omega$. This value should permit the $4.7\text{-k}\Omega$ resistor to pull the configuration pin to a valid logic low level. The pull-up resistor is enabled only during $\overline{\text{HRESET}}$ (and for platform/system clocks after $\overline{\text{HRESET}}$ deassertion to ensure capture of the reset value). When the input receiver is disabled the pull-up is also, thus allowing functional operation of the pin as an output with minimal signal quality or delay disruption. The default value for all configuration bits treated this way has been encoded such that a high voltage level puts the device into the default state and external resistors are needed only when non-default settings are required by the user.

Careful board layout with stubless connections to these pull-down resistors coupled with the large value of the pull-down resistor should minimize the disruption of signal quality or speed for output pins thus configured.

The platform PLL ratio and e500 PLL ratio configuration pins are not equipped with these default pull-up devices.

17.7 Pull-Up Resistor Requirements

The MPC8541E requires high resistance pull-up resistors (10 k Ω is recommended) on open drain type pins.

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 52. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion give unpredictable results.

TSEC1_TXD[3:0] must not be pulled low during reset. Some PHY chips have internal pulldowns that could cause this to happen. If such PHY chips are used, then a pullup must be placed on these signals strong enough to restore these signals to a logical 1 during reset.

Refer to the PCI 2.2 specification for all pull-ups required for PCI.

17.8 JTAG Configuration Signals

Boundary-scan testing is enabled through the JTAG interface signals. The TRST signal is optional in the IEEE 1149.1 specification, but is provided on all processors that implement the Power Architecture. The device requires TRST to be asserted during reset conditions to ensure the JTAG boundary logic does not interfere with normal chip operation. While it is possible to force the TAP controller to the reset state using only the TCK and TMS signals, generally systems assert TRST during the power-on reset flow. Simply tying TRST to HRESET is not practical because the JTAG interface is also used for accessing the common on-chip processor (COP) function.



System Design Information



Notes:

- 1. The COP port and target board should be able to independently assert HRESET and TRST to the processor in order to fully control the processor as shown here.
- 2. Populate this with a 10 Ω resistor for short-circuit/current-limiting protection.
- 3. The KEY location (pin 14) is not physically present on the COP header.
- 4. Although pin 12 is defined as a No-Connect, some debug tools may use pin 12 as an additional GND pin for improved signal integrity.
- This switch is included as a precaution for BSDL testing. The switch should be open during BSDL testing to avoid accidentally asserting the TRST line. If BSDL testing is not being performed, this switch should be closed or removed.
- 6. Asserting SRESET causes a machine check interrupt to the e500 core.

Figure 52. JTAG Interface Connection



18 Document Revision History

Table 51 provides a revision history for this hardware specification.

Rev. No.	Date	Substantive Change(s)
4.2	1/2008	Added "Note: Rise/Fall Time on CPM Input Pins" and following note text to Section 10.2, "CPM AC Timing Specifications."
4.1	07/2007	Inserted Figure 3, ""Maximum AC Waveforms on PCI interface for 3.3-V Signaling."
4	12/2006	Updated Section 2.1.2, "Power Sequencing." Updated back page information.
3.2	11/2006	Updated Section 2.1.2, "Power Sequencing." Replaced Section 17.8, "JTAG Configuration Signals."
3.1	10/2005	Table 4: Added footnote 2 about junction temperature.Table 4: Added max. power values for 1000 MHz core frequency.Removed Figure 3, "Maximum AC Waveforms on PCI Interface for 3.3-V Signaling."Table 30: Modified note to tLBKSKEW from 8 to 9Table 30: Changed tLBKHOZ1 and tLBKHOV2 values.Table 30: Added note 3 to tLBKHOV1.Table 30 and Table 31: Modified note 3.Table 31: Added note 3 to tLBKLOV1.Table 31: Modified values for tLBKHKT, tLBKLOV1, tLBKLOV2, tLBKLOV3, tLBKLOZ1, and tLBKLOZ2.Figure 21: Changed Input Signals: LAD[0:31]/LDP[0:3].Table 43: PCI1_CLK and PCI2_CLK changed from I/O to I.Table 52: Added column for Encryption Acceleration.
3	8/29/2005	Table 4: Modified max. power values. Table 43: Modified notes for signals TSEC1_TXD[3:0], TSEC2_TXD[3:0], TRIG_OUT/READY, MSRCID4, and MDVAL.
2	8/2005	Previous revision's history listed incorrect cross references. Table 2 is now correctly listed as Table 27 and Table 31 is now listed as Table 31. Table 7: Added note 2. Table 14: Modified min and max values for t _{DDKHMP}
1	6/2005	Table 27: Changed LV _{dd} to OV _{dd} for the supply voltage Ethernet management interface.Table 4: Modified footnote 4 and changed typical power for the 1000MHz core frequency.Table 31: Corrected symbols for body rows 9–15, effectively changing them from a high state to a low state.
0	6/2005	Initial Release.